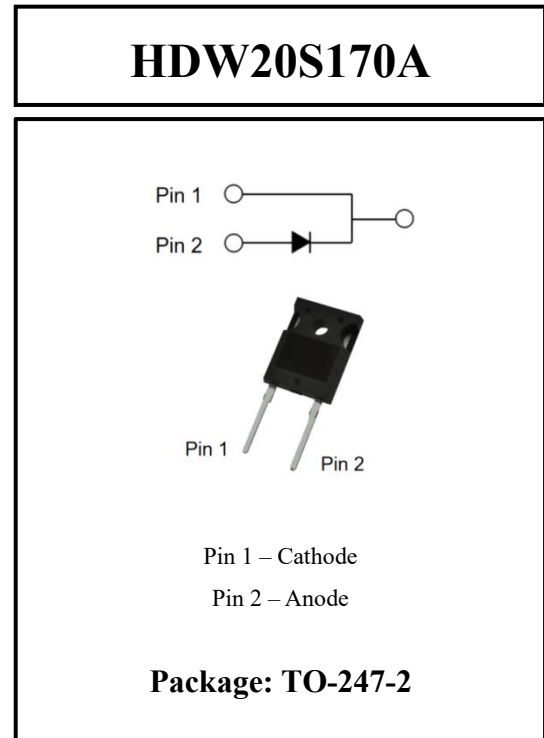


Silicon Carbide Schottky Diode (SiC SBD)

1. Product Features:

- Revolutionary semiconductor material - Silicon Carbide
- Temperature independent switching behavior
- Low forward voltage even at high operating temperature
- Excellent thermal performance
- Specified dv/dt ruggedness
- Qualified according to JEDEC for target applications
- Pb-free lead plating; RoHS compliant



2. Product Applications

- Solar Inverters
- Uninterruptable Power Supplies (UPS)
- Motor drives
- Power Factor Correction (PFC)
- Switch Mode Power Supplies (SMPS)
- On Board Charger (OBC)

3. Typical Performance Parameters

Tab.1. Typical Performance Parameters

Type	V_{DC}	I_F	Q_C	T_{vjmax}	Marking	Package
HDW20S170A	1700V	20A	192nC	175°C	D20S0170	TO-247-2

4. Maximum Ratings

Tab.2. Maximum Ratings

Parameters	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	1700	V
Surge Peak Reverse Voltage	V_{RSM}	1700	V
Continuous Forward Current , $T_c = 25^\circ\text{C}$ $T_c = 125^\circ\text{C}$ $T_c = 150^\circ\text{C}$	I_F	70 39 26	A
Repetitive Peak Forward Surge Current $T_c = 25^\circ\text{C}, t_p = 10\text{ms}$	I_{FRM}	100	
Non-Repetitive Peak Forward Surge Current $T_c = 25^\circ\text{C}, t_p = 10\text{ms}, \text{Half Sine Wave}$	I_{FSM}	94	
Non-Repetitive Peak Forward Current $T_c = 25^\circ\text{C}, t_p = 10\mu\text{s}$	$I_{F, max}$	1200	
Power Dissipation $T_c = 25^\circ\text{C}$ $T_c = 110^\circ\text{C}$	P_{tot}	468 203	W
Operating Junction	T_j	-55 to +175	°C
Storage Temperature	T_{stg}	-55 to +175	

5. Thermal Properties

Tab.3. Thermal Properties

Parameters	Symbol	Conditions	Typ. value	Unit
Thermal resistance (junction - case)	$R_{th(j-c)}$		0.32	°C/W

6. Electrical Characteristics

Tab.4. Static Characteristic ($T_{vj} = 25^{\circ}\text{C}$, unless otherwise specified)

Parameters	Symbol	Conditions	Min. value	Typ. value	Max. value	Unit
DC blocking voltage	V_{DC}	$T_j = 25^{\circ}\text{C}$	1700	-	-	V
Diode forward voltage	V_F	$I_F = 20\text{A}, T_j = 25^{\circ}\text{C}$ $I_F = 20\text{A}, T_j = 175^{\circ}\text{C}$	-	1.5 2.4	1.8 2.7	V
Reverse current	I_R	$V_R = 1700\text{V}, T_j = 25^{\circ}\text{C}$ $V_R = 1700\text{V}, T_j = 175^{\circ}\text{C}$	-	1.5 19	100 200	μA

Tab.5. Dynamic Characteristic ($T_{vj} = 25^{\circ}\text{C}$, unless otherwise specified)

Parameters	Symbol	Conditions	Min. value	Typ. value	Max. value	Unit
Total capacitive charge	Q_C	$V_R = 1700\text{V}, Q_C = \int_0^{V_R} C(V)dV$	-	192	-	nC
Total Capacitance	C	$V_R = 0\text{V}, f = 1\text{MHz}$ $V_R = 800\text{V}, f = 1\text{MHz}$ $V_R = 1700\text{V}, f = 1\text{MHz}$	-	1740 82 79	-	pF
Capacitance Stored Energy	E_C	$V_R = 1700\text{V}$	-	202	-	μJ

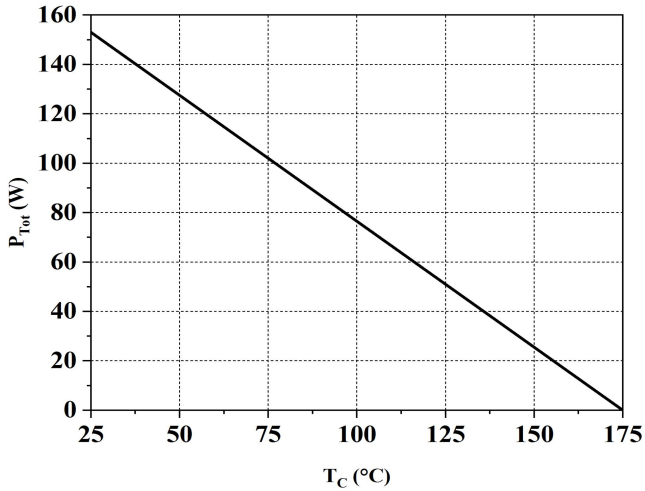


Fig.1. Power dissipation as a function of case temperature

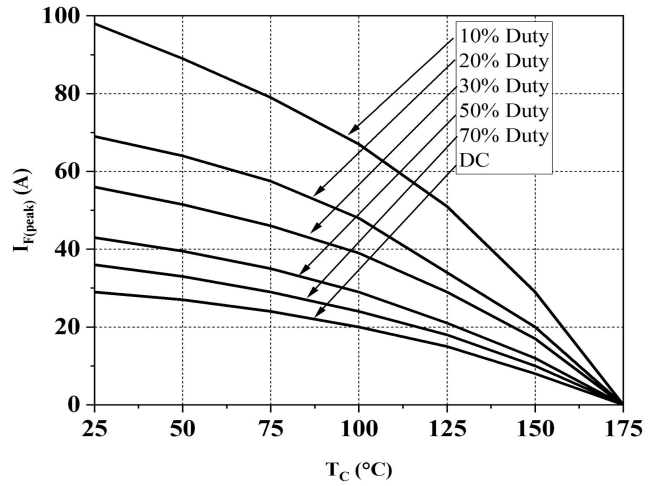


Fig.2. Diode forward current as function of case temperature

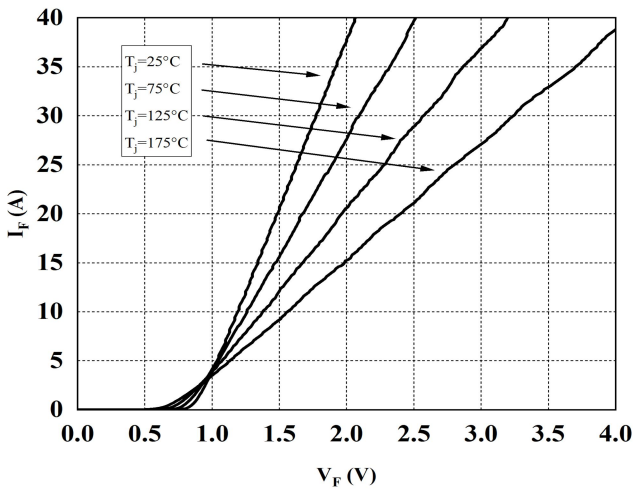


Fig.3. Typical forward characteristics 1700

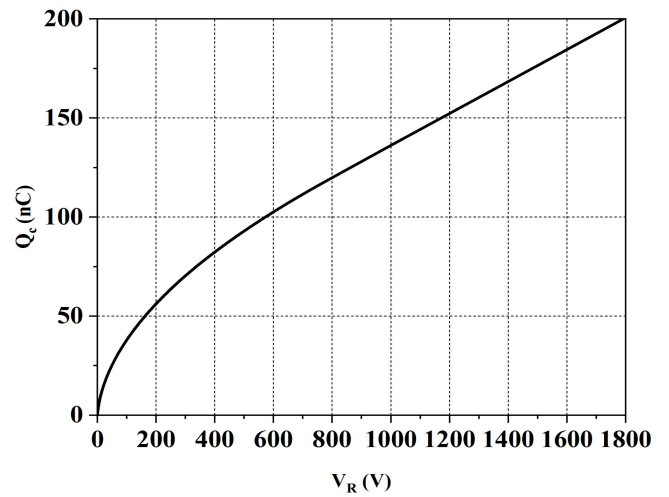


Fig.4. Typical capacitance charge as function of reverse voltage

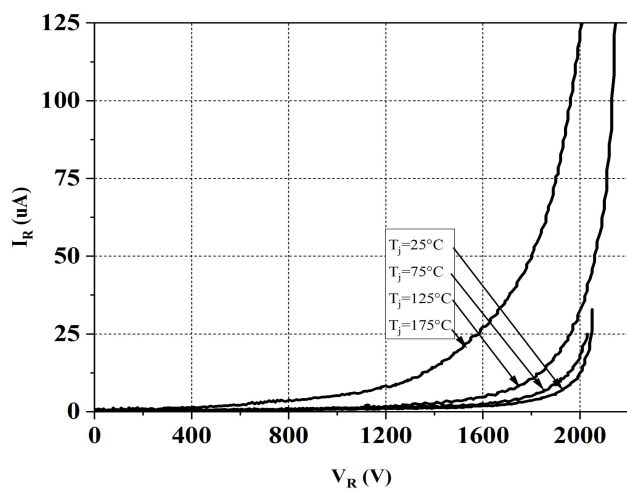


Fig.5. Typical reverse current as function of reverse voltage

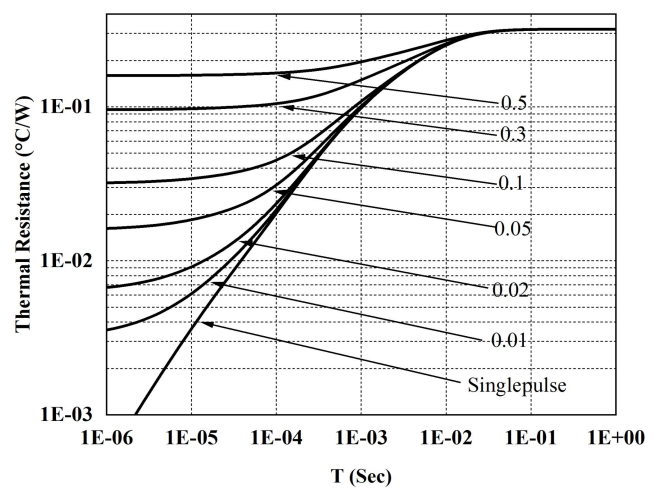


Fig.6. Max. transient thermal impedance
D=tp/T

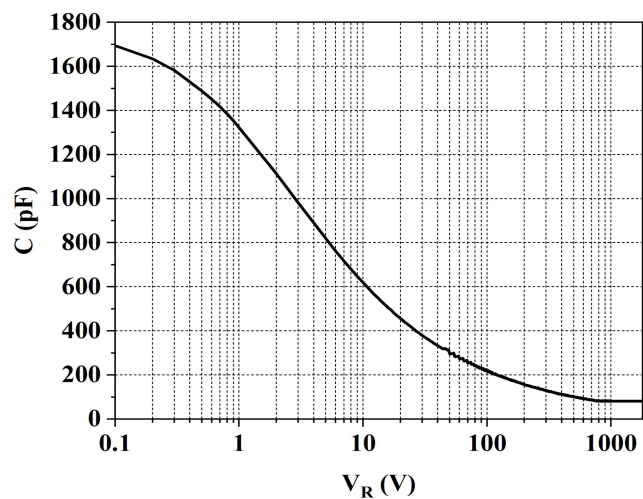


Fig.7. Typical capacitance as function of reverse voltage

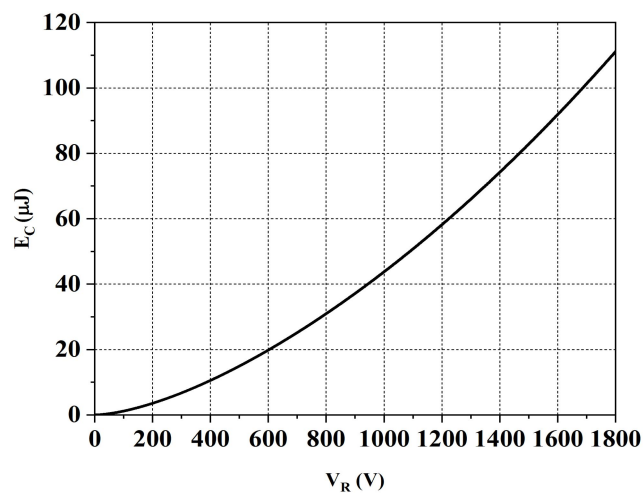
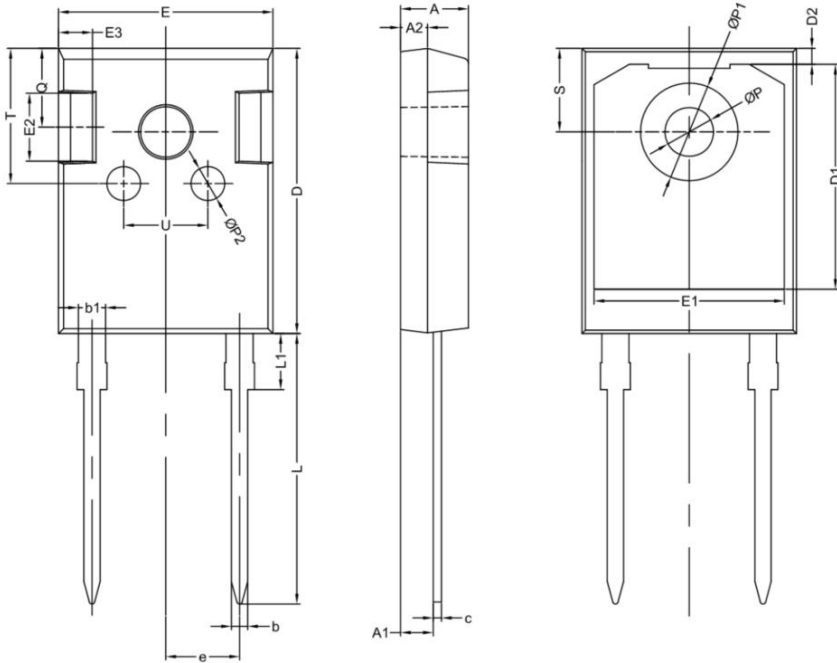


Fig.8. Typical capacitance stored energy as function of reverse voltage

7. Package Dimensions



COMMON DIMENSIONS			
(UNITS OF MEASURE=MILLIMETRE)			
SYMBOL	MIN	TYP	MAX
A	4.80	5.00	5.20
A1	2.21	2.41	2.61
A2	1.90	2.00	2.10
b	1.10	1.20	1.35
b1		2.00	
c	0.55	0.60	0.75
D	20.80	21.00	21.20
D1		16.58	
D2		1.17	
E	15.60	15.80	16.00
E1		14.02	
E2		5.00	
E3		2.50	
e		5.44	
L	19.42	19.92	20.42
L1		4.13	
P	3.50	3.60	3.70
P1	3.30	7.19	
P2	2.99	2.50	
Q	2.50	5.80	
S	6.05	6.15	6.25
T		10.00	
U		6.20	

8. Version Information

Version No.	Status	Date changed	Version revision record
V1.0	Preview edition	2021/11	
V1.1	Preview edition	2022/01	